

A B S T R A C T

AN EDGE-EMITTING TUNABLE SEMICONDUCTOR LASER

5 The invention concerns a tunable edge-emitting
semiconductor laser (10) including a resonant cavity
delimited by two reflectors (15, 20), one of which is a
fixed reflector (15) and the other of which is a mobile
reflector (20), and including an active section (1) with
10 gain of length L_1 and a tunable section (2) of length L_2 ,
characterized in that the total length of the cavity
 $L = L_1 + L_2$ is less than or equal to $20 \mu\text{m}$.

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35 Translation of the title and the abstract as they were when originally filed by the
Applicant. No account has been taken of any changes that may have been made
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38.2, and/or 48.3.